In the Specification:

On Page 1, immediately following the title, please insert the following paragraph:

-- This application is a continuation of U.S. Application Serial No. 09/787,528, filed March 20, 2001, which is a Section 371 of International Application PCT/JP00/00072, filed January 13, 2000, and the entire disclosures of which are hereby incorporated by reference. --

On Page 14, paragraph beginning at line 5 and continuing through page 15, has been rewritten as indicated below:

Plugs, which are each formed of a main conductive film 15 coated with adjacent conductive films (first conductive films) 14a and 14b for preventing diffusion, are respectively formed in contact holes formed in the insulating film 13, and are connected to the diffusion layers 2, 3, 4, and 5. A multilayer interconnection, which is formed of a main conductive film 17 coated with adjacent conductive films 16a and 16b for preventing diffusion, is connected through these plugs. This multilayer interconnection can be obtained by a process in which, for instance, grooves for interconnection are formed in an insulating film 18, and after the adjacent conductive film 16a is formed thereon by such as chemical vapor deposition, the main conductive film 17 is formed by such as plating, followed by the formation of the adjacent conductive film 16b thereon by such as chemical vapor deposition. On top of this multilayer interconnection, a plug, which is formed of a main conductive film 20 coated with an adjacent conductive film 19, is formed in a contact hole formed in an insulating film 21, and is connected to the aforementioned multilayer interconnection. A second multilayer interconnection, which is formed of a main conductive film 23 coated with adjacent conductive films 22a and 22b, is connected through this plug. This second multilayer interconnection can be obtained by a process in which, for instance, grooves for interconnection are formed in an insulating film 24, and after the adjacent conductive film 22a is formed thereon by

such as chemical vapor deposition, the main conductive film 23 is formed by such as plating, followed by the formation of the adjacent conductive film 22b thereon by such as chemical vapor deposition. An insulating film 25 is then formed over the conductive film 22b and the insulating film 24.

On Page 36, paragraph beginning at line 27 and continuing through pages 37 and 38, has been rewritten as indicated below:

Further, Fig. 15 shows a cross-sectional structure of principal portions of a semiconductor device in accordance with a fourth embodiment of the invention. The difference of the fourth embodiment from the first embodiment lies in that the interconnection layer formed by the main conductive film 17 is connected via a conductive plug 32 to a gate electrode 29 formed on a gate insulating film 28. In this case, since the gate electrode 29 is in contact with the conductive plug 32 and an insulating film 30, to improve the reliability it suffices if the constituent elements of the gate electrode 29 are selected such that all of the following requirements are met: that the difference $\{|ap - an|/ap\} \times 100 = A(\%)$ between the short side an in the unit rectangular cell of the closest packed crystal plane formed by the main constituent element of the gate electrode 29 and the short side ap in the unit rectangular cell of the closest packed crystal plane formed by the main constituent element of the conductive plug 32 and the difference $\{|bp - bn|/bp\} \times 100 = B(\%)$ between the long side bn in the unit rectangular cell of the closest packed crystal plane formed by the main constituent element of the gate electrode 29 and the long side bp in the unit rectangular cell of the closest packed crystal plane formed by the main constituent element of the conductive plug 32 satisfy the inequality $\{A + B \times (ap/bp)\} < 13\%$, that the melting point of the main constituent element of the gate electrode 29 is not less than 1.4 times that of the main constituent element of the conductive plug 32, that the gate electrode 29 contains at least one different kind of element in addition to the main constituent element, that the difference between the atomic radius of at least one kind of added element among the different kinds of elements and the atomic radius of the main constituent element of the gate electrode 29 is not more than 10%, and that the bond energy between the added element and silicon (Si) is not less than 1.9 times that of the main constituent element of the gate